Supporting Information

Achieving Over 30% Photon-to-Photon Efficiency with Tandem OLED Structures in Organic Upconversion Devices

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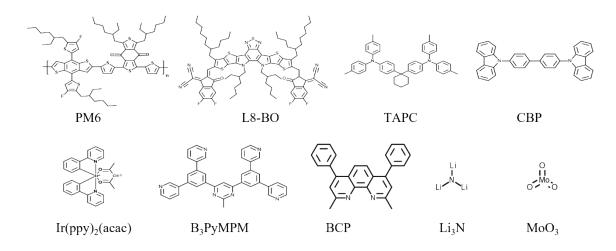


Figure S1. The molecular structures of the materials utilized in this work.

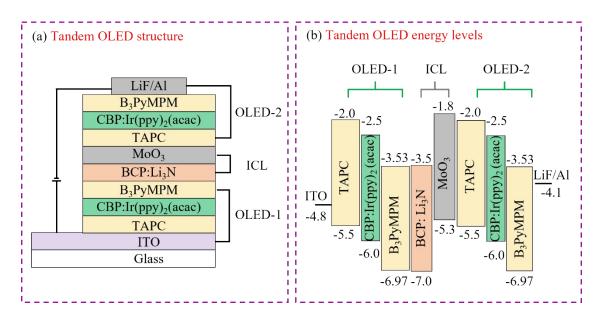


Figure S2. Tandem OLED structure and principles. (a) Schematic diagram of the structure; (b) Energy level diagram.

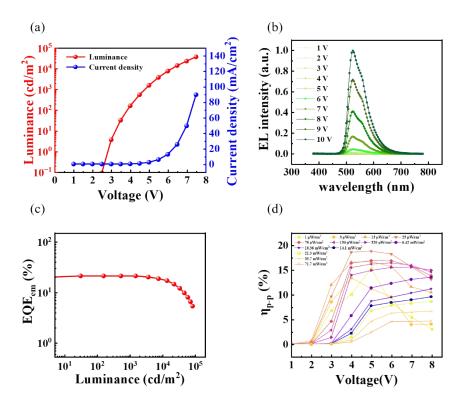


Figure S3. Performance of single OLED. (a) J-V-L characteristic curves of a single OLED; (b) Electroluminescence spectra at different bias voltages; (c) EQE_{em} at various luminance levels; (d) η_{p-p} of the OUD based on a single OLED.

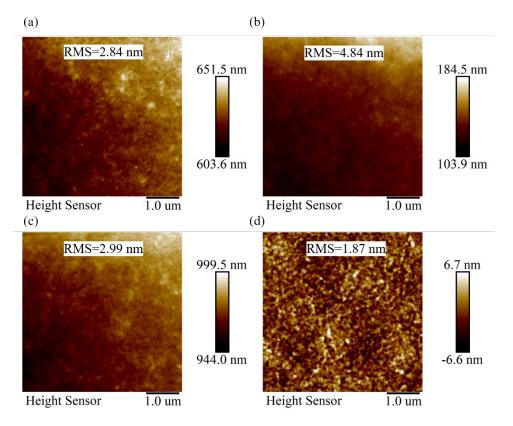


Figure S4. AFM characterization of film surfaces. (a) OLED-1 film; (b) OLED- $1/BCP:Li_3N/MoO_3$ film; (c) OLED- $1/BCP:Li_3N/MoO_3/OLED-2$ film; (d) standalone PM6:L8-BO film.

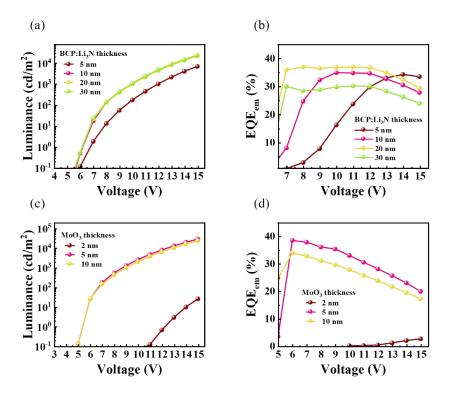


Figure S5. Impact of ICL thickness on tandem OLED performance. (a) Effect of BCP:Li₃N layer thickness on luminance; (b) Effect of BCP:Li₃N layer thickness on EQE_{em}; (c) Effect of MoO₃ layer thickness on EQE_{em}.

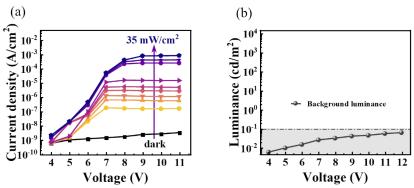


Figure S6. (a) J-V characteristics under different incident light power densities; (b) Background luminance under different bias voltages

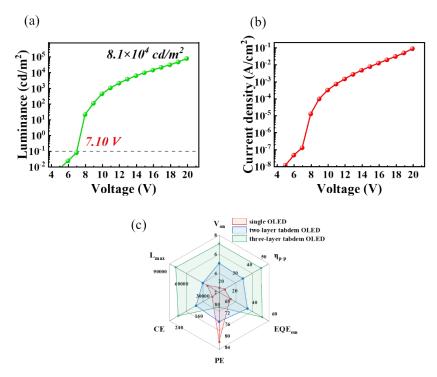


Figure S7. Performance characterization of the three-layer tandem OLED. (a) L-V characteristics; (b) J-V characteristics. (c) The performance comparison of devices with different numbers of tandem OLEDs.

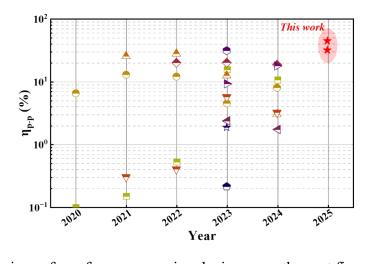


Figure S8. Comparison of $\eta_{p\text{-}p}$ for upconversion devices over the past five years.

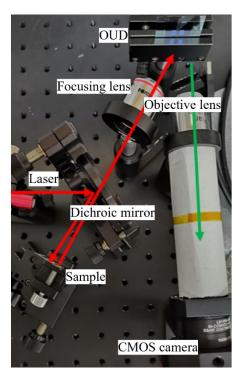


Figure S9. Practical optical path for upconversion imaging of infrared reflected light from samples.